## **SanRex**

## **THYRISTOR / DIODE (ISOLATED TYPE)**

# PK(PD)160FG40/80/120/160

 $I_{T(AV)} = 160A$ ,  $V_{RRM} = 400 - 1600V$ 

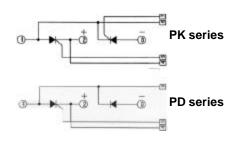
SanRex Thyristor/Thyristor modules (**PK series**), Thyristor/Diode modules (**PD series**) are designed for general purpose high voltage applications such as motor controls, temperature controls, lighting controls and UPS.

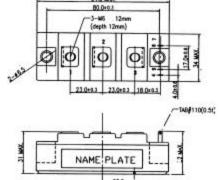
#### **Features**

- \* Glass-passivated junctions Features
- \* High Surge Current
- \* Low loss (V<sub>TM</sub>=1.5V)

### Typical Applications

- \* Motor Controls
- \* Temperature Controls
- \* Lighting Controls





(Tj = 25°C unless otherwise noted)

< Maximum Ratings >	(Tj = 25°C unle	ess ot

Symbol	Itom		Ratings					Linit
	Item	PK160FG40	PK160FG80	PK160FC	G120	Unit		
$V_{RRM}$	Repetitive Pe	eak Reverse Voltage	400	800	1200		1600	٧
$V_{RSM}$	Non-Repetiti	ve Peak Reverse Voltage	480	960	1300		1700	V
$V_{DRM}$	Repetitive Pe	eak Off-state Voltage	400	800	1200	)	1600	V
I <sub>T(AV)</sub>	Average On-	state Current	T <sub>C</sub> = 84°C		160			Α
I <sub>T(RMS)</sub>	R.M.S. On-st	tate Current	T <sub>C</sub> = 84°C 251				251	Α
I <sub>TSM</sub>	Surge On-sta	rge On-state Current  1/2 cycle, 50Hz/60Hz, Peak value, Non-repetitive				Α		
l²t	I <sup>2</sup> t (for fusing	g)	Value for one cycle surge current			125000		$A^2$ s
P <sub>GM</sub>	Peak Gate Power Dissipation						10	
P <sub>G(AV)</sub>	Average Gat	e Power Dissipation	3					W
I <sub>FGM</sub>	Peak Gate C	urrent	3				3	Α
V <sub>FG M</sub>	Peak Gate Voltage (Forward)						10	V
V <sub>RG M</sub>	Peak Gate Voltage (Reverse)					5		V
di/dt	Critical Rate of Rise of On-state Current		I <sub>G</sub> =100mA, V <sub>D</sub> =1/2V <sub>DRM</sub> , dig/dt=0.1A/Fs			s 200		A/Fs
V <sub>ISO</sub>	Isolation Breakdown Voltage		A.C. 1 minute			2500		
Tj	Operating Ju	nction Temperature				-40 to +125		°C
T <sub>stg</sub>	Storage Temperature						-40 to +125	°C
	Mounting	Mounting M6	Recommended Value 2.5 to		)	4.7		N*m
	Torque	Terminals M6	Recommende	d Value 2.5 to 3.9	)		4.7	
	Mass		Typical Value			210		g

#### < Electrical Characteristics >

(Tj = 25°C unless otherwise noted)

Symbol	Item	Conditions	Ratings			Unit
			Min.	Тур.	Max.	Unit
I <sub>DRM</sub>	Repetitive Peak Off-state Current	$T_j = 125$ °C, $V_D = V_{DRM}$			35	mΑ
I <sub>RRM</sub>	Repetitive Peak Reverse Current	$T_j = 125$ °C, $V_R = V_{RRM}$			35	mA
$V_{TM}$	Peak On-State Voltage	I <sub>T</sub> = 480A			1.5	٧
I <sub>GT</sub>	Gate Trigger Current	VD=6V, IT=1A			100	mΑ
V <sub>GT</sub>	Gate Trigger Voltage	VD=6V, IT=1A			3	V
V <sub>G D</sub>	Non-Trigger Gate Voltage	$Tj = 125^{\circ}C, V_D=1/2V_{DRM}$	0.25			V
dv/dt	Critical Rate of Rise of Off-state Voltage	$Tj = 125^{\circ}C, V_D = 2/3V_{DRM}$	500			W/Fs
Rth(j-c)	Thermal Resistance	Junction to case			0.18	°C/W